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FIELD EFFECT TRANSISTOR, AND

~~SEMICONDUCTOR DEVICE MANUFACTURING METHOD~~

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to a MOS (Metal Oxide Semiconductor) field effect transistor whose  
5 blocking voltage appearing between a drain electrode and a substrate (between a drain electrode and a source electrode) is higher than 5 volts inclusive.

Description of Related Art

For implementing a flash memory or the like  
10 device which requires a voltage of about 10 volts or higher for memory cell write/erase operations, there are required MOS field effect transistors (MOSFETs) whose blocking voltage is on the order of 10 volts. In Japanese Patent Application Laid-Open Publication  
15 No. 86580/1995 (JP-A-7-86580), a MOS field effect transistor which exhibits a relatively high blocking voltage of about 30 volts and in which a high-density layer formed in contact with a drain electrode is disposed relative to a high-density layer formed in  
20 contact with the source electrode with interposition of an insulation film having a thickness greater than a gate insulation film.

Further, as the MOS field effect transistor